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- a first mark formed at a predetermined position with respect to an active layer on a face opposed to a substrate to which the chip is mounted; and

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4. A semiconductor laser diode chip as claimed in claim 1,
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width as that of said active layer.

6. A semiconductor laser diode chip as claimed in claim 1, wherein

said second mark is constructed by a pair of marks formed on both sides of said active layer.

7. A semiconductor laser diode chip as claimed in claim 6, wherein

said second mark has a circular shape.

8. A semiconductor laser diode chip as claimed in claim 7, wherein

said substrate side mark has a circular shape having a diameter different from that of said second mark.

9. A semiconductor laser diode chip as claimed in claim 1, wherein

a plurality of said substrate side marks and a plurality of said second marks are formed, respectively.

10. A mounting method of a semiconductor laser diode chip having an active layer, for mounting the SEMICONDUCTOR LASER DIODE chip to a substrate at its predetermined position;

said semiconductor laser diode comprising:

a first mark formed in the vicinity of said active layer; and

a second positioning mark with respect to said substrate;

said substrate having a substrate side mark formed at a

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position opposed to said second mark when said semiconductor laser diode chip is arranged in the predetermined position;

the mounting method including:

a process for measuring a position relation of said active layer and said second mark;

a process for setting said second mark and said substrate side mark to be opposed to each other and arranging said semiconductor laser diode chip in said substrate; and

a process for correcting the position of said semiconductor laser diode chip on the basis of said position relation and fixing said semiconductor laser diode chip to said substrate.

11. A mounting method of a semiconductor laser diode chip as claimed in claim 10, wherein

said second mark is constructed by a thin line pattern formed along said active layer in the vicinity of this active layer.

12. A mounting method of a semiconductor laser diode chip as claimed in claim 11, wherein

said thin line pattern is constructed by a metallic film formed in plural thin parallel straight lines.

13. A mounting method of a semiconductor laser diode chip as claimed in claim 10, wherein

said second mark is constructed by a thin line formed at an upper portion of said active layer.

14. A mounting method of a semiconductor laser diode chip as claimed in claim 13, wherein

said second mark has approximately the same width as that of said active layer.

5 15. A mounting method of a semiconductor laser diode chip as claimed in claim 9, wherein

said first mark is constructed by a pair of marks formed on both sides of said active layer.

16. A mounting method of a semiconductor laser diode chip as claimed in claim 15, wherein

said first mark has a circular shape.

17. A mounting method of a semiconductor laser diode chip as claimed in claim 15, wherein

15 said substrate side mark has a circular shape having a diameter different from that of said second mark.

18. A mounting method of a semiconductor laser diode chip as claimed in claim 10, wherein

each of said first and second marks is constructed by a metallic thin film and is formed by the same process.

20 19. A mounting method of a semiconductor laser diode chip as claimed in claim 10, wherein

said substrate has a V-groove the center of which coincides with the central axis of said active layer.

25 20. A mounting method of a semiconductor laser diode chip as claimed in claim 10, wherein

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a plurality of said substrate side marks and a plurality of said second marks are formed, respectively.

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